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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10046739	FILING DATE 01/17/2002	CLASS 438	SUBCLASS 500 ⁺	GAU 2812	EXAMINER [REDACTED]
**APPLICANTS: Yamada Hisashi; Fukuhara Noboru; Hata Masahiko;					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED: JAPAN 2001-009143 01/17/2001					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/> RESCIND <input type="checkbox"/>					
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners's initials				ATTORNEY DOCKET NO 3885-0101P	
TITLE : Thin-film crystal wafer having pn junction and method for fabricating the wafer					

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED		
			Total Claims	Print Claim for O.G.	
ISSUE FEE		Primary Examiner	DRAWING		
Amount Due	Date Paid		Sheets Drwg.	Figs.Drwg.	Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner		
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